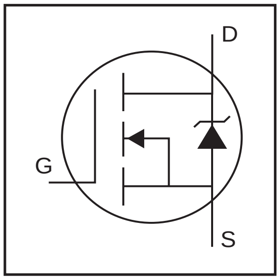
International
IOR Rectifier

IRFPS3815PbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



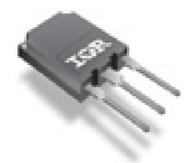
V_{DSS} = 150V

$R_{DS(on)}$ = 0.015Ω

I_D = 105A

Description

The HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.



Super-247™

Absolute Maximum Ratings

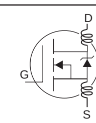
	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	105	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	74	
I_{DM}	Pulsed Drain Current ①	390	
P_D @T_C = 25°C	Power Dissipation	441	W
	Linear Derating Factor	2.9	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy②	1610	mJ
I_{AR}	Avalanche Current①	58	A
E_{AR}	Repetitive Avalanche Energy①	38	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

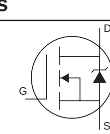
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	0.34	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	——	
$R_{\theta JA}$	Junction-to-Ambient	——	40	

09/13/04

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.18	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.015	Ω	V_{GS} = 10V, I_D = 63A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–––	5.0	V	V_{DS} = 10V, I_D = 250µA
g_{fs}	Forward Transconductance	47	–––	–––	S	V_{DS} = 50V, I_D = 58A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	µA	V_{DS} = 100V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -30V
Q_g	Total Gate Charge	–––	260	390	nC	I_D = 58A
Q_{gs}	Gate-to-Source Charge	–––	53	80		V_{DS} = 120V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	150	230		V_{GS} = 10V④
$t_{d(on)}$	Turn-On Delay Time	–––	22	–––	ns	V_{DD} = 75V
t_r	Rise Time	–––	130	–––		I_D = 58A
$t_{d(off)}$	Turn-Off Delay Time	–––	51	–––		R_G = 1.03Ω
t_f	Fall Time	–––	60	–––		V_{GS} = 10V ④
L_D	Internal Drain Inductance	–––	5.0	–––	nH	Between lead, 6mm (0.25in.)
L_S	Internal Source Inductance	–––	13	–––		from package and center of die contact 
C_{iss}	Input Capacitance	–––	6810	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	1570	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	480	–––		ƒ = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	–––	9820	–––		V_{GS} = 0V, V_{DS} = 1.0V, ƒ = 1.0MHz
C_{oss}	Output Capacitance	–––	670	–––		V_{GS} = 0V, V_{DS} = 120V, ƒ = 1.0MHz
C_{oss} eff.	Effective Output Capacitance ⑤	–––	1270	–––		V_{GS} = 0V, V_{DS} = 0V to 120V

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	105	A	MOSFET symbol showing the
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	390		integral reverse p-n junction diode. 
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 58A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	270	410	ns	T_J = 25°C, I_F = 58A
Q_{rr}	Reverse RecoveryCharge	–––	2990	4490	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 0.96mH R_G = 25Ω, I_{AS} = 58A. (See Figure 12)

③ $I_{SD} \leq$ 58A, di/dt ≤ 450A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

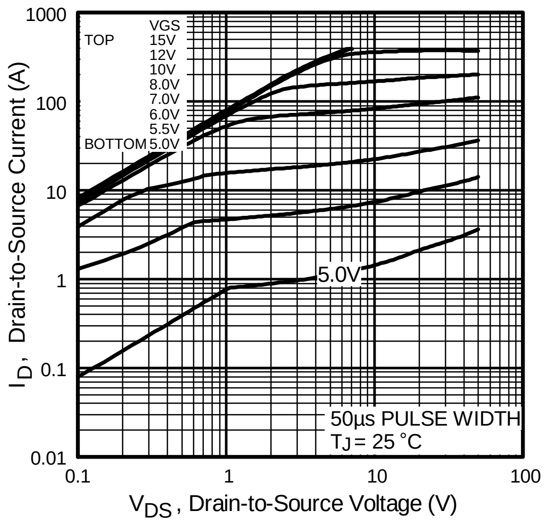


Fig 1. Typical Output Characteristics

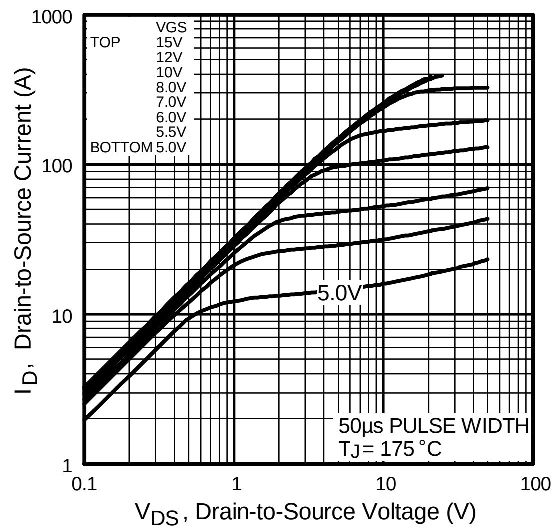


Fig 2. Typical Output Characteristics

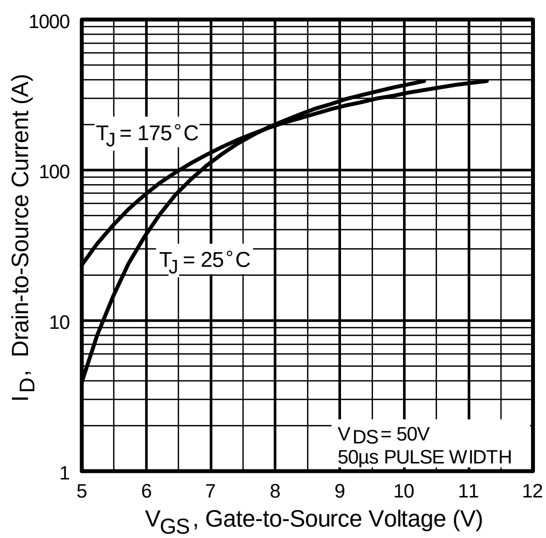


Fig 3. Typical Transfer Characteristics

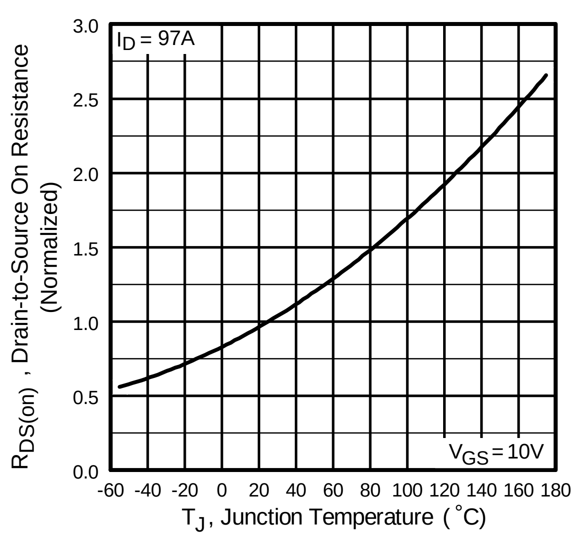


Fig 4. Normalized On-Resistance Vs. Temperature

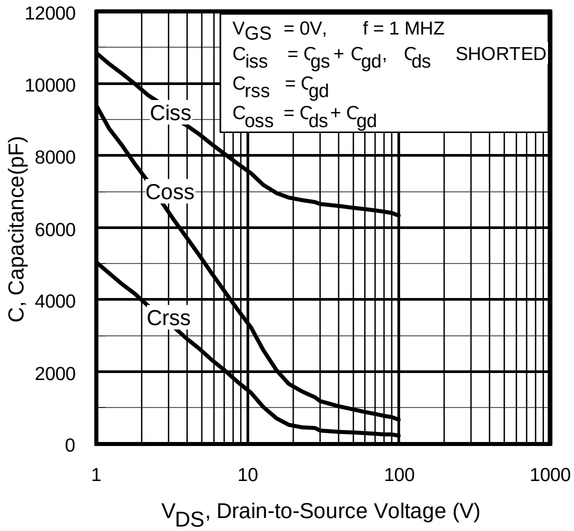


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

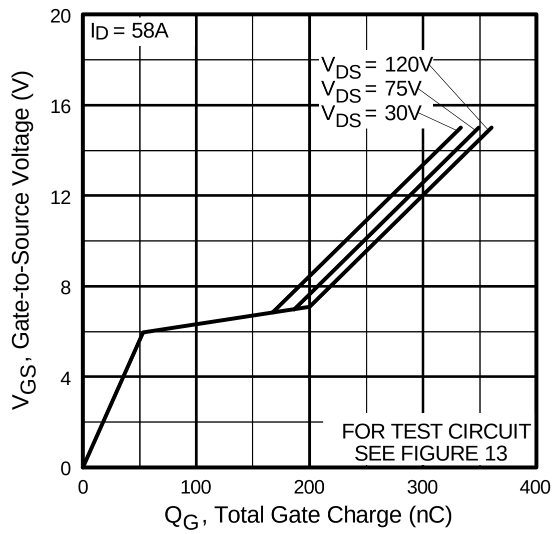


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

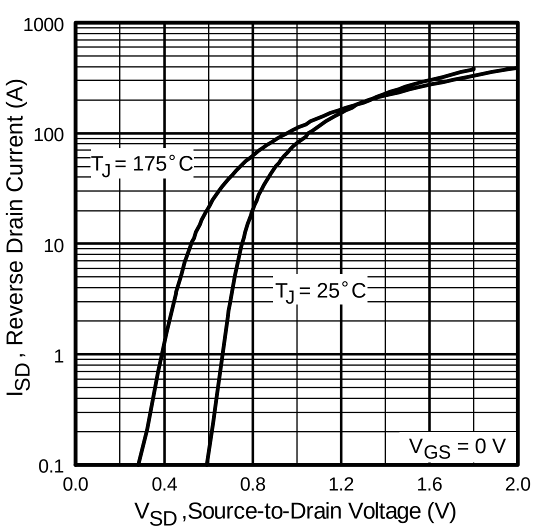


Fig 7. Typical Source-Drain Diode Forward Voltage

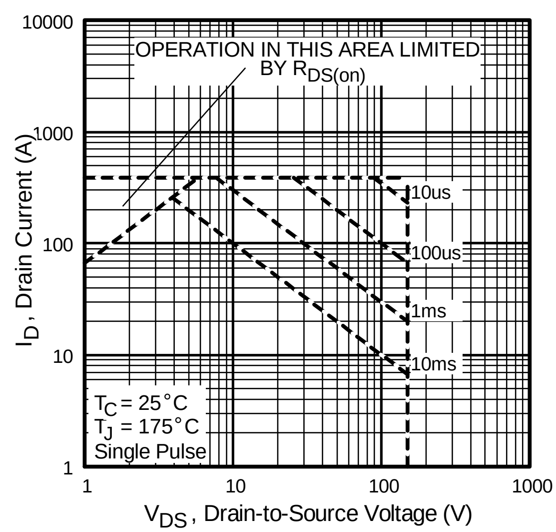


Fig 8. Maximum Safe Operating Area

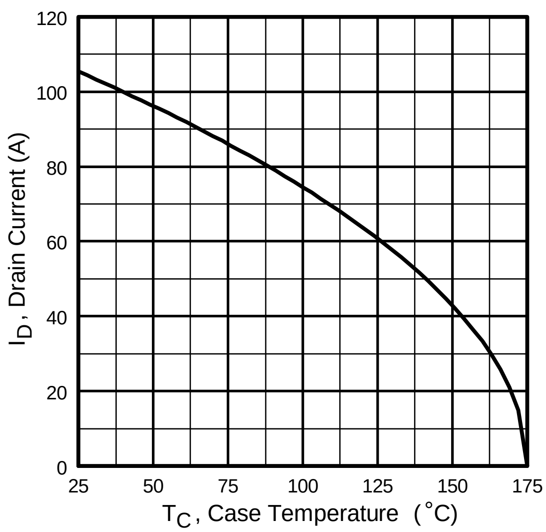
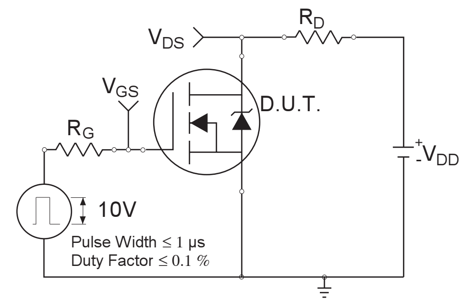
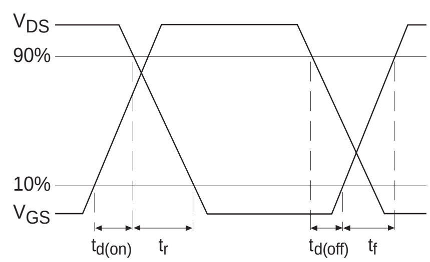


Fig 9. Maximum Drain Current Vs. Case Temperature





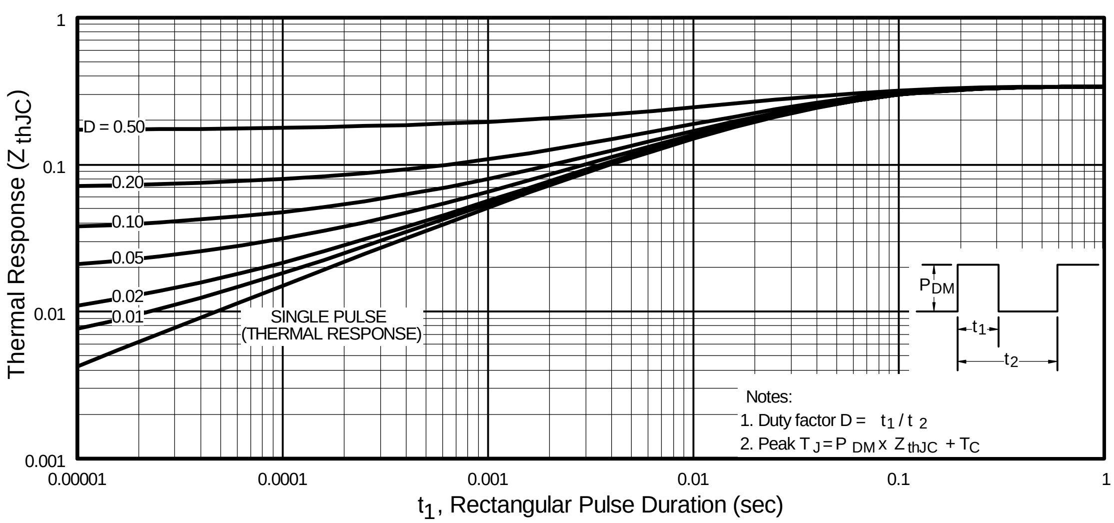


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

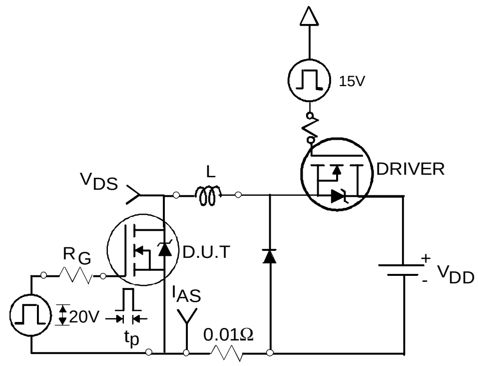


Fig 12a. Unclamped Inductive Test Circuit

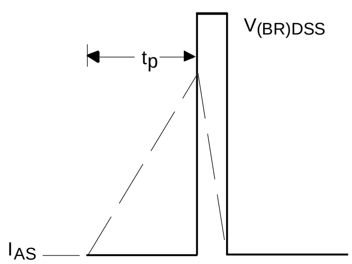


Fig 12b. Unclamped Inductive Waveforms

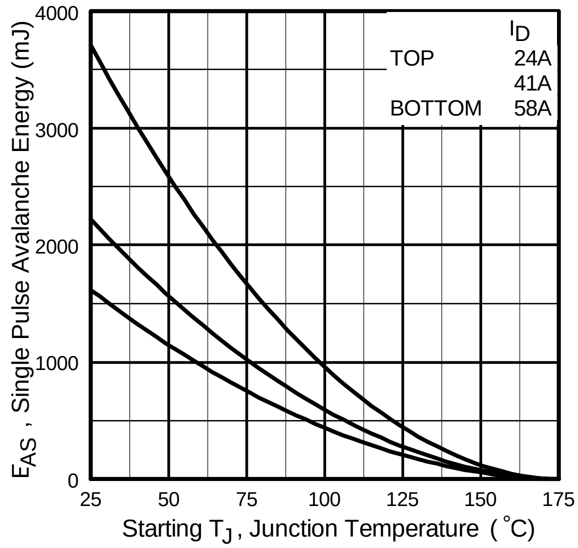


Fig 12c. Maximum Avalanche Energy
Vs. Drain Current

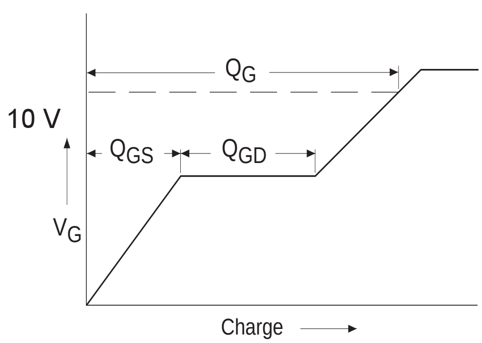


Fig 13a. Basic Gate Charge Waveform

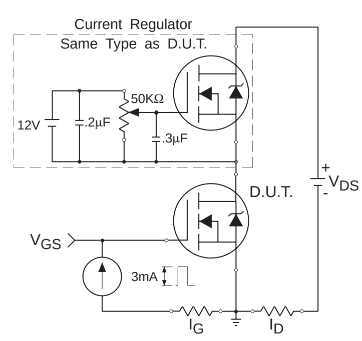
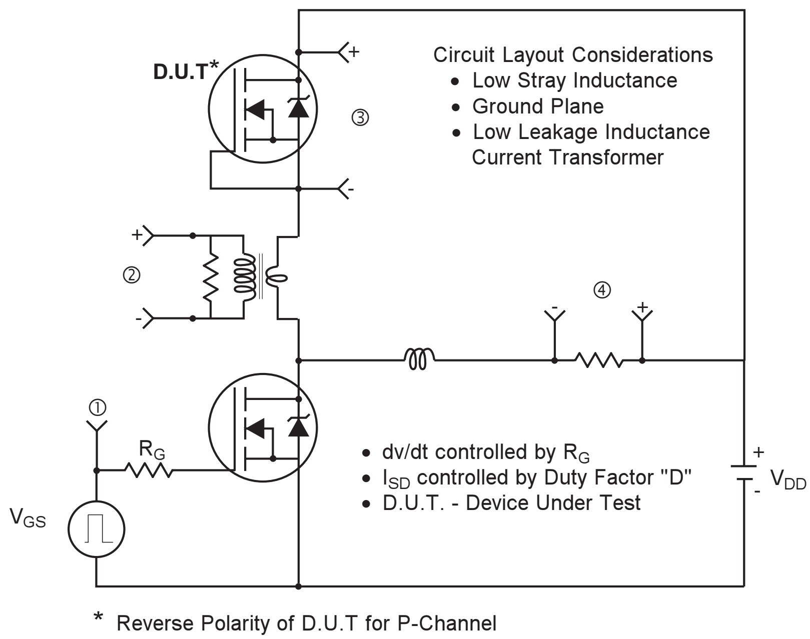
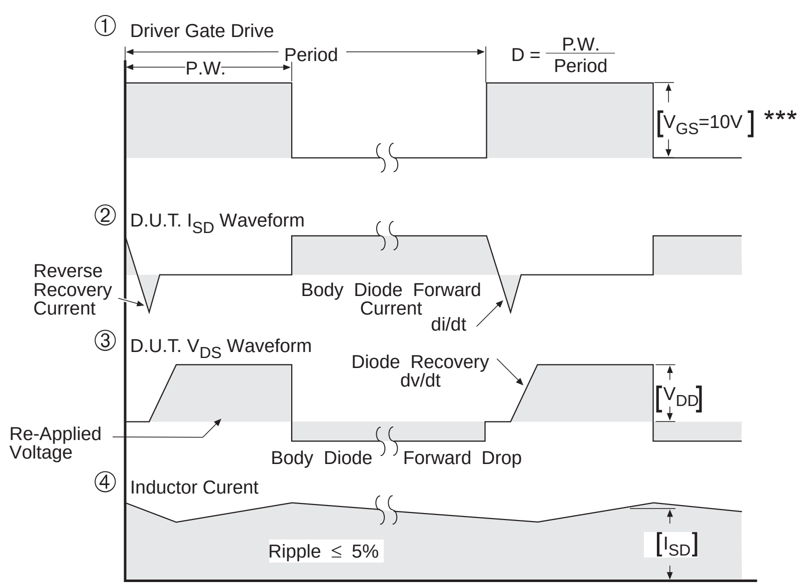


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

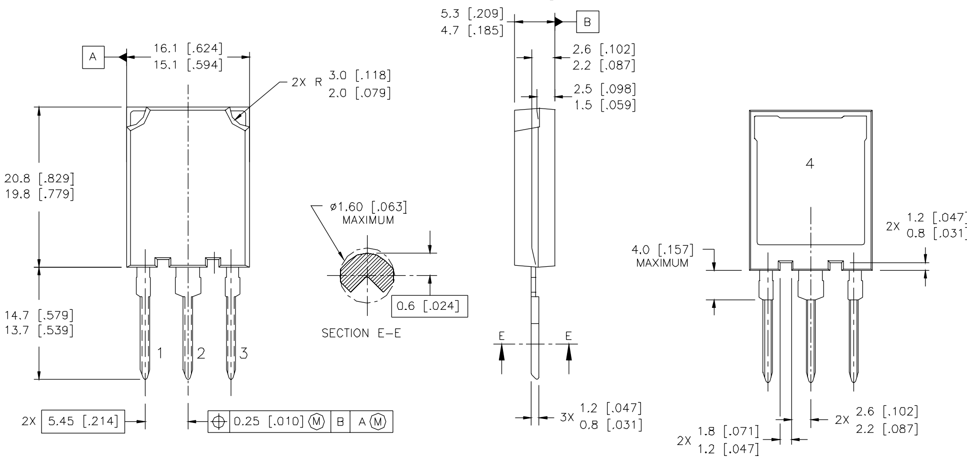




*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

Case Outline and Dimensions — Super-247



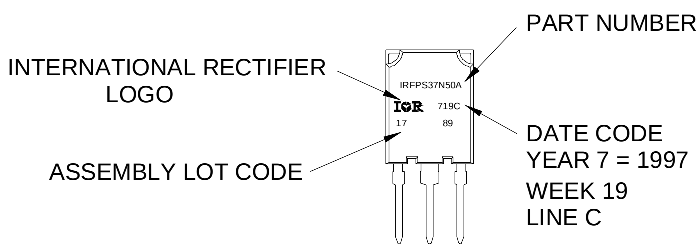
NOTES:
1. DIMENSIONS & TOLERANCING PER ASME Y14.5M-1994
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETRES [INCHES]

LEAD ASSIGNMENTS

MOSFET	IGBT
1 - GATE	1 - GATE
2 - DRAIN	2 - COLLECTOR
3 - SOURCE	3 - EMITTER
4 - DRAIN	4 - COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position
indicates "Lead-Free"

TOP

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
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IMPORTANT NOTICE

WARNINGS